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**INFORMATION DISCLOSURE
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Complete if Known

Application Number	10/028643
Filing Date	December 20, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2823
Examiner Name	Pham, Long

Sheet 1 of 5

Attorney Docket No: 1303.030US1

US PATENT DOCUMENTS

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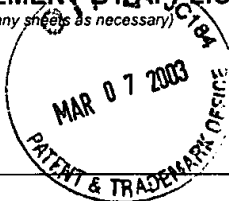
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Examiner Name	Pham, Long

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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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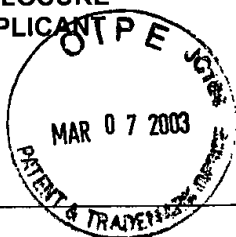
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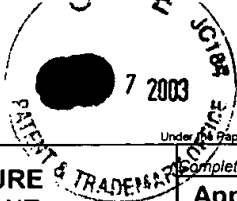
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Sheet 4 of 5

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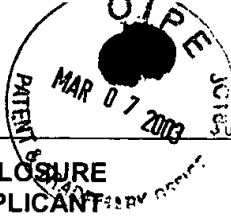
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